

# Akira Uedono

## List of Publications by Year in descending order

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419  
papers

7,096  
citations

81743

39  
h-index

110170

64  
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422  
all docs

422  
docs citations

422  
times ranked

5066  
citing authors

#	ARTICLE	IF	CITATIONS
1	Impurity diffusion in ion implanted AlN layers on sapphire substrates by thermal annealing. Japanese Journal of Applied Physics, 2022, 61, 026501.	0.8	8
2	Structure-Property Relationships of Polysilsesquioxanes for Thermal Insulation Materials. ACS Applied Polymer Materials, 2022, 4, 2851-2859.	2.0	7
3	Negatively charged boron vacancy center in diamond. Physical Review B, 2022, 105, .	1.1	3
4	Impacts of Si-doping on vacancy complex formation and their influences on deep ultraviolet luminescence dynamics in Al <sub>x</sub> Ga <sub>1-x</sub> N films and multiple quantum wells grown by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2022, 61, 050501.	0.8	4
5	Organic-Inorganic Hybrid Thermal Insulation Materials Prepared via Hydrosilylation of Polysilsesquioxane Having Hydrosilyl Groups and Triallylisocyanurate. ACS Applied Polymer Materials, 2022, 4, 3726-3733.	2.0	5
6	Effect of Ultra-High-Pressure Annealing on Defect Reactions in Ion-Implanted GaN Studied by Positron Annihilation. Physica Status Solidi (B): Basic Research, 2022, 259, .	0.7	7
7	Effect of conversion on epoxy resin properties: Combined molecular dynamics simulation and experimental study. Polymer, 2022, 254, 125041.	1.8	8
8	Effects of Hydrogen Incorporation on Mg Diffusion in GaN Doped with Mg Ions via Ultra-High-Pressure Annealing. Physica Status Solidi (B): Basic Research, 2022, 259, .	0.7	8
9	Thermal Insulating Property of Silsesquioxane Hybrid Film Induced by Intramolecular Void Spaces. ACS Applied Polymer Materials, 2021, 3, 3383-3391.	2.0	10
10	Interfacial Conductivity Enhancement and Pore Confinement Conductivity-Lowering Behavior inside the Nanopores of Solid Silica-gel Nanocomposite Electrolytes. ACS Applied Materials & Interfaces, 2021, 13, 40543-40551.	4.0	9
11	Reduced nonradiative recombination rates in <i>c</i> -plane Al <sub>0.83</sub> In <sub>0.17</sub> N films grown on a nearly lattice-matched GaN substrate by metalorganic vapor phase epitaxy. Applied Physics Letters, 2021, 119, .	1.5	5
12	Effect of Ag doping on crystallinity and microstrain of LaMnO <sub>3</sub> nanoparticles: Confirmations of defect levels with positron lifetime and Doppler-broadening calculations. Physica B: Condensed Matter, 2021, 615, 413087.	1.3	6
13	Vacancy-type defects in bulk GaN grown by oxide vapor phase epitaxy probed using positron annihilation. Journal of Crystal Growth, 2021, 570, 126219.	0.7	6
14	Optical and electrical properties of silicon-implanted $\hat{\Gamma}$ -Al <sub>2</sub> O <sub>3</sub> . Japanese Journal of Applied Physics, 2021, 60, 106502.	0.8	2
15	Growth of Al <sub>x</sub> Ga <sub>1-x</sub> N/In <sub>y</sub> Ga <sub>1-y</sub> N hetero structure on AlN/sapphire templates exhibiting Shubnikov-de Haas oscillation. Journal of Crystal Growth, 2021, 574, 126324.	0.7	0
16	Dopant activation process in Mg-implanted GaN studied by monoenergetic positron beam. Scientific Reports, 2021, 11, 20660.	1.6	12
17	Low-temperature annealing behavior of defects in Mg-ion-implanted GaN studied using MOS diodes and monoenergetic positron beam. Japanese Journal of Applied Physics, 2021, 60, 016502.	0.8	9
18	Improved minority carrier lifetime in p-type GaN segments prepared by vacancy-guided redistribution of Mg. Applied Physics Letters, 2021, 119, .	1.5	13

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19	Vacancy complexes acting as midgap recombination centers in (Al,Ga)N semiconductors. , 2021, , .		0
20	Pore structure analysis of ionic liquid-templated porous silica using positron annihilation lifetime spectroscopy. Microporous and Mesoporous Materials, 2020, 295, 109964.	2.2	4
21	Preparation and characterization of cellulose acetate membranes with TEMPO-oxidized cellulose nanofibrils containing alkyl ammonium carboxylates. Cellulose, 2020, 27, 1357-1365.	2.4	6
22	Morphological characterization and mechanical behavior by dicing and thinning on direct bonded Si wafer. Journal of Manufacturing Processes, 2020, 58, 811-818.	2.8	8
23	Dynamic Observation and Theoretical Analysis of Initial O <sub>2</sub> Molecule Adsorption on Polar and <i>m</i>-Plane Surfaces of GaN. Journal of Physical Chemistry C, 2020, 124, 25282-25290.	1.5	10
24	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. Scientific Reports, 2020, 10, 17349.	1.6	22
25	Selective trapping of positrons by Ag nanolayers in a V/Ag multilayer system. AIP Advances, 2020, 10, 035012.	0.6	3
26	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. Journal of Applied Physics, 2020, 128, .	1.1	24
27	Hole capture-coefficient of intrinsic nonradiative recombination centers that commonly exist in bulk, epitaxial, and proton-irradiated ZnO. Journal of Applied Physics, 2020, 127, 215704.	1.1	6
28	The Influence of AlN Nucleation Layer on Radio Frequency Transmission Loss of AlN <sub>x</sub> on <sub>y</sub> Si Heterostructure. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900755.	0.8	8
29	Voids and vacancy-type defects in SiO <sub>2</sub> /GaN structures probed by monoenergetic positron beams. Journal of Applied Physics, 2020, 127, .	1.1	7
30	Effect of Free-Volume Hole Fraction on Dynamic Mechanical Properties of Epoxy Resins Investigated by Pressure <sup>2</sup> Volume <sup>2</sup> Temperature Technique. Journal of Physical Chemistry B, 2020, 124, 1824-1832.	1.2	4
31	Effect of free-volume holes on static mechanical properties of epoxy resins studied by positron annihilation and PVT experiments. Polymer, 2020, 190, 122225.	1.8	21
32	Magnetic properties of metastable bcc phase in Fe <sub>64</sub> Ni <sub>36</sub> alloy synthesized through polyol process. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	1.1	13
33	Origin and dynamic properties of major intrinsic nonradiative recombination centers in wide bandgap nitride semiconductors. , 2020, , .		2
34	Control of vacancy-type defects in Mg implanted GaN studied by positron annihilation spectroscopy. , 2020, , .		0
35	Annealing Behaviours of Open Spaces in Thin Al <sub>2</sub> O <sub>3</sub> Films Deposited on Semiconductors Studied Using Monoenergetic Positron Beams. Acta Physica Polonica A, 2020, 137, 227-230.	0.2	0
36	Calculation of Positron States and Annihilation Parameters in Gamma and Amorphous Al <sub>2</sub> O <sub>3</sub> . Acta Physica Polonica A, 2020, 137, 231-234.	0.2	1

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37	Free Volume in Epoxy Resins for CFRP Studied by Means of Positron Annihilation. Journal of the Japan Society for Precision Engineering, 2020, 86, 206-209.	0.0	0
38	Growth of high-quality GaN by halogen-free vapor phase epitaxy. Applied Physics Express, 2020, 13, 085509.	1.1	6
39	Defect Identification in Bonding Surface Layers by Positron Annihilation Spectroscopy. , 2019, , .		0
40	Room temperature photoluminescence lifetime for the near-band-edge emission of epitaxial and ion-implanted GaN on GaN structures. Japanese Journal of Applied Physics, 2019, 58, SC0802.	0.8	25
41	Er <sup>3+</sup> induced point defects in ZnO and impact of Li <sup>+</sup> /Na <sup>+</sup> /K <sup>+</sup> on the vacancy defects in ZnO:Er studied by positron annihilation spectroscopy. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	1.1	7
42	Computational study of positron annihilation parameters for cation mono-vacancies and vacancy complexes in nitride semiconductor alloys. Journal of Physics Condensed Matter, 2019, 31, 475401.	0.7	14
43	Influence of post-deposition annealing on interface characteristics at Al <sub>2</sub> O <sub>3</sub> /n-GaN. , 2019, , .		3
44	Investigation of Al <sub>2</sub> O <sub>3</sub> /GaN interface properties by sub-bandgap photo-assisted capacitance-voltage technique. AIP Advances, 2019, 9, .	0.6	17
45	Impact of defects on the electrical properties of p <sup>+</sup> n diodes formed by implanting Mg and H ions into N-polar GaN. Journal of Applied Physics, 2019, 126, .	1.1	13
46	Characterization of the distribution of defects introduced by plasma exposure in Si substrate. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, .	0.9	14
47	Structural disorder and in-gap states of Mg-implanted GaN films evaluated by photothermal deflection spectroscopy. Journal of Crystal Growth, 2019, 511, 15-18.	0.7	10
48	Two-dimensional mapping of hydrogen and other elements in materials with microbeam-based transmission ERDA and PIXE. Nuclear Instruments & Methods in Physics Research B, 2019, 450, 319-322.	0.6	3
49	Annealing Behavior of Vacancy-type Defects in Mg- and H-implanted GaN Studied Using Monoenergetic Positron Beams. Physica Status Solidi (B): Basic Research, 2019, 256, 1900104.	0.7	27
50	Free volumes introduced by fractures of CFRP probed using positron annihilation. Composites Part A: Applied Science and Manufacturing, 2019, 122, 54-58.	3.8	10
51	Vacancy-type defects in GaN self-assembled nanowires probed using monoenergetic positron beam. Journal of Applied Physics, 2019, 125, 175705.	1.1	1
52	Simple way of finding Ba to Si deposition rate ratios for high photoresponsivity in BaSi <sub>2</sub> films by Raman spectroscopy. Applied Physics Express, 2019, 12, 055506.	1.1	30
53	Effect of dopant concentration and annealing of Yttrium doped CuO nanocrystallites studied by positron annihilation spectroscopy. Journal of Alloys and Compounds, 2019, 788, 549-558.	2.8	16
54	<i>(Invited)</i> A Novel Optical Characterization of a-Si:H/c-Si Interface Microstructures Based on Data of Positron Annihilation Spectroscopy. ECS Transactions, 2019, 92, 21-24.	0.3	0

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55	Effect of illumination on positron states in wide bandgap semiconductors. AIP Conference Proceedings, 2019, , .	0.3	0
56	Photoluminescence Studies of Sequentially Mg and H Ion-implanted GaN with Various Implantation Depths and Crystallographic Planes. , 2019, , .		1
57	In-plane optical polarization and dynamic properties of the near-band-edge emission of an m-plane freestanding AlN substrate and a homoepitaxial film. Applied Physics Letters, 2019, 115, 151903.	1.5	11
58	Valence band edge tail states and band gap defect levels of GaN bulk and In <sub>x</sub> Ga <sub>1-x</sub> N films detected by hard X-ray photoemission and photothermal deflection spectroscopy. Applied Physics Express, 2018, 11, 021002.	1.1	17
59	Ion energy control and its applicability to plasma enhanced atomic layer deposition for synthesizing titanium dioxide films. Thin Solid Films, 2018, 660, 865-870.	0.8	7
60	Vacancy-type defects in Al <sub>2</sub> O <sub>3</sub> /GaN structure probed by monoenergetic positron beams. Journal of Applied Physics, 2018, 123, .	1.1	21
61	Effect of ion energies on the film properties of titanium dioxides synthesized via plasma enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	0.9	10
62	Carrier Trapping by Vacancy-Type Defects in Mg-Implanted GaN Studied Using Monoenergetic Positron Beams. Physica Status Solidi (B): Basic Research, 2018, 255, 1700521.	0.7	60
63	AlN metal-semiconductor field-effect transistors using Si-ion implantation. Japanese Journal of Applied Physics, 2018, 57, 04FR11.	0.8	42
64	The origins and properties of intrinsic nonradiative recombination centers in wide bandgap GaN and AlGaN. Journal of Applied Physics, 2018, 123, .	1.1	112
65	Synthesis and characterization of titanium silicon oxide thin films prepared by plasma enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	0.9	4
66	Room-temperature photoluminescence lifetime for the near-band-edge emission of (0001) p-type GaN fabricated by sequential ion-implantation of Mg and H. Applied Physics Letters, 2018, 113, .	1.5	40
67	(Invited) Vacancy-Type Defects and Their Carrier Trapping Properties in GaN Studied by Monoenergetic Positron Beams. ECS Transactions, 2018, 86, 149-160.	0.3	0
68	Fast Optical Characterization of Microvoid Size in Hydrogenated Amorphous Silicon: Study on the Universal Applicability of the Correlation between the Microvoid Size and the Optical Constant. , 2018, , .		0
69	Annealing behavior of open spaces in AlON films studied by monoenergetic positron beams. Applied Physics Letters, 2018, 112, .	1.5	5
70	Large electron capture-cross-section of the major nonradiative recombination centers in Mg-doped GaN epilayers grown on a GaN substrate. Applied Physics Letters, 2018, 112, .	1.5	55
71	Polarity-dependence of the defect formation in c-axis oriented ZnO by the irradiation of an 8 MeV proton beam. Journal of Applied Physics, 2018, 123, 161562.	1.1	6
72	Positron Annihilation Studies on Chemically Synthesized FeCo Alloy. Scientific Reports, 2018, 8, 9764.	1.6	13

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73	Behavior of copper contamination on backside damage for ultra-thin silicon three dimensional stacking structure. <i>Microelectronic Engineering</i> , 2017, 167, 23-31.	1.1	18
74	Effect of Free-Volume Holes on Dynamic Mechanical Properties of Epoxy Resins for Carbon-Fiber-Reinforced Polymers. <i>Macromolecules</i> , 2017, 50, 3933-3942.	2.2	54
75	Prediction of positron-annihilation parameters for vacancy-type defects in ternary alloy semiconductors by data-scientific approach. <i>Journal of Physics: Conference Series</i> , 2017, 791, 012023.	0.3	1
76	Nitrogen vacancies as a common element of the green luminescence and nonradiative recombination centers in Mg-implanted GaN layers formed on a GaN substrate. <i>Applied Physics Express</i> , 2017, 10, 061002.	1.1	70
77	Development of a microbeam PIXE system for additive light elements in structural materials. <i>Nuclear Instruments &amp; Methods in Physics Research B</i> , 2017, 404, 92-95.	0.6	2
78	Influence of Si wafer thinning processes on (sub)surface defects. <i>Applied Surface Science</i> , 2017, 404, 82-87.	3.1	22
79	Effect of La doping on the lattice defects and photoluminescence properties of CuO. <i>Journal of Alloys and Compounds</i> , 2017, 709, 496-504.	2.8	73
80	Synthesis, defect characterization and photocatalytic degradation efficiency of Tb doped CuO nanoparticles. <i>Advanced Powder Technology</i> , 2017, 28, 3026-3038.	2.0	61
81	Carrier activation in Mg implanted GaN by short wavelength Nd:YAG laser thermal annealing. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1700225.	0.8	18
82	Electron capture by vacancy-type defects in carbon-doped GaN studied using monoenergetic positron beams. <i>Thin Solid Films</i> , 2017, 639, 78-83.	0.8	11
83	Vacancy-type defects in bulk GaN grown by the Na-flux method probed using positron annihilation. <i>Journal of Crystal Growth</i> , 2017, 475, 261-265.	0.7	15
84	Defect-Resistant Radiative Performance of $m$ -Plane Immiscible $\text{Al}_{1-x}\text{In}_x\text{N}$ Epitaxial Nanostructures for Deep-Ultraviolet and Visible Polarized Light Emitters. <i>Advanced Materials</i> , 2017, 29, 1603644.	11.1	38
85	Vacancy-Type Defects in GaN for Power Devices Probed by Positron Annihilation. <i>Defect and Diffusion Forum</i> , 2017, 373, 183-188.	0.4	0
86	Investigation on photoluminescence properties and defect chemistry of $\text{GdAlO}_3:\text{Dy}^{3+}$ $\text{Ba}^{2+}$ phosphors. <i>Optical Materials</i> , 2016, 58, 524-530.	1.7	12
87	Vacancy-type defects in Mg-implanted GaN probed by a monoenergetic positron beam. , 2016, , .		1
88	Computational studies of positron states and annihilation parameters in semiconductors – vacancy-type defects in group-III nitrides –. <i>Journal of Physics: Conference Series</i> , 2016, 674, 012020.	0.3	8
89	Electronic and optical characteristics of an $m$ -plane GaN single crystal grown by hydride vapor phase epitaxy on a GaN seed synthesized by the ammonothermal method using an acidic mineralizer. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FA03.	0.8	4
90	Enhanced photo/electroluminescence properties of Eu-doped GaN through optimization of the growth temperature and Eu related defect environment. <i>APL Materials</i> , 2016, 4, 056103.	2.2	22

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91	Probing the effect of point defects on the leakage blocking capability of Al <sub>0.1</sub> Ga <sub>0.9</sub> N/Si structures using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2016, 120, .	1.1	15
92	Characterization of Extreme Si Thinning Process for Wafer-to-Wafer Stacking. , 2016, , .		13
93	Vacancy-type defects in Mg-doped GaN grown by ammonia-based molecular beam epitaxy probed using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2016, 119, 245702.	1.1	9
94	Controlling the carrier lifetime of nearly threading-dislocation-free ZnO homoepitaxial films by 3 <i>d</i> transition-metal doping. <i>Applied Physics Letters</i> , 2016, 108, .	1.5	9
95	Vacancy behavior in Cu(In <sub>1-x</sub> Ga <sub>x</sub> )Se <sub>2</sub> layers grown by a three-stage coevaporation process probed by monoenergetic positron beams. <i>Thin Solid Films</i> , 2016, 603, 418-423.	0.8	9
96	Vacancy defects and defect clusters in alkali metal ion-doped MgO nanocrystallites studied by positron annihilation and photoluminescence spectroscopy. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	1.1	10
97	Surface sealing using self-assembled monolayers and its effect on metal diffusion in porous low- <i>k</i> dielectrics studied using monoenergetic positron beams. <i>Applied Surface Science</i> , 2016, 368, 272-276.	3.1	22
98	Vacancies and electron trapping centers in acidic ammonothermal GaN probed by a monoenergetic positron beam. <i>Journal of Crystal Growth</i> , 2016, 448, 117-121.	0.7	22
99	Nanopores formation and shape evolution in Ge during intense ionizing irradiation. <i>Microporous and Mesoporous Materials</i> , 2016, 225, 323-330.	2.2	8
100	Impacts of Dislocations and Point Defects on the Internal Quantum Efficiency of the Near-Band-Edge Emission in AlGaIn-Based DUV Light-Emitting Materials. <i>Springer Series in Materials Science</i> , 2016, , 115-136.	0.4	2
101	Positron annihilation and cathodoluminescence study on inductively coupled plasma etched GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 913-916.	0.7	5
102	Vacancy-type defects and their annealing behaviors in Mg-implanted GaN studied by a monoenergetic positron beam. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 2794-2801.	0.7	65
103	Recent Progress in Gas Barrier Thin Film Coatings on PET Bottles in Food and Beverage Applications. <i>Coatings</i> , 2015, 5, 987-1001.	1.2	43
104	Thermal Behavior of Residual Defects in Low-Dose Arsenic- and Boron-Implanted Silicon After High-Temperature Rapid Thermal Annealing. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2015, 28, 92-95.	1.4	8
105	Enhancement of the gas barrier property of polypropylene by introducing plasma-treated silane coating with SiO <sub>x</sub> -modified top-surface. <i>Surface and Coatings Technology</i> , 2015, 284, 377-383.	2.2	11
106	Polarity dependent radiation hardness of GaN. , 2015, , .		0
107	Effect of incorporation of deuterium on vacancy-type defects of a-C:H films prepared by plasma CVD. <i>Applied Surface Science</i> , 2015, 330, 142-147.	3.1	4
108	Free Volume Profiles at Polymer-Solid Interfaces Probed by Focused Slow Positron Beam. <i>Macromolecules</i> , 2015, 48, 1493-1498.	2.2	9



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109	Vacancies in In <sub>x</sub> Ga <sub>1-x</sub> N/GaN multiple quantum wells fabricated on <i>m</i> -plane GaN probed by a monoenergetic positron beam. Applied Physics Express, 2015, 8, 051002.	1.1	3
110	Low-resistivity <i>m</i> -plane freestanding GaN substrate with very low point-defect concentrations grown by hydride vapor phase epitaxy on a GaN seed crystal synthesized by the ammonothermal method. Applied Physics Express, 2015, 8, 095501.	1.1	21
111	Investigation on photoluminescence, electrical and positron lifetime of Eu <sup>3+</sup> activated Gd <sub>2</sub> O <sub>3</sub> phosphors. Materials Chemistry and Physics, 2015, 166, 73-81.	2.0	7
112	Molecular motion and relaxation below glass transition temperature in poly (methyl methacrylate) studied by positron annihilation. Radiation Physics and Chemistry, 2015, 108, 81-86.	1.4	15
113	Vacancy-type defects induced by grinding of Si wafers studied by monoenergetic positron beams. Journal of Applied Physics, 2014, 116, 134501.	1.1	12
114	Optically active vacancies in GaN grown on Si substrates probed using a monoenergetic positron beam. Applied Physics Letters, 2014, 104, 082110.	1.5	22
115	Impact of back-grinding-induced damage on Si wafer thinning for three-dimensional integration. Japanese Journal of Applied Physics, 2014, 53, 05GE04.	0.8	30
116	Leaching properties of chromate-containing epoxy films using radiotracers, PALS and SEM. Progress in Organic Coatings, 2014, 77, 257-267.	1.9	35
117	Residual defects in low-dose arsenic-implanted silicon after high-temperature annealing. Nuclear Instruments & Methods in Physics Research B, 2014, 321, 54-58.	0.6	6
118	Native and process induced defects in GaN films grown on Si substrates probed using a monoenergetic positron beam. , 2014, , .		0
119	Vacancy clusters introduced by CF <sub>4</sub> -based plasma treatment in GaN probed with a monoenergetic positron beam. Applied Physics Express, 2014, 7, 121001.	1.1	5
120	Annealing behaviors of vacancy-type defects near interfaces between metal contacts and GaN probed using a monoenergetic positron beam. Applied Physics Letters, 2014, 105, 052108.	1.5	11
121	Investigation of defect related photoluminescence property of multicolour emitting Gd <sub>2</sub> O <sub>3</sub> :Dy <sup>3+</sup> phosphor. RSC Advances, 2014, 4, 34257.	1.7	47
122	Characterization of polyethylene terephthalate films coated with thin Al <sub>x</sub> Si <sub>1-x</sub> O <sub>y</sub> layers using monoenergetic positron beams. Thin Solid Films, 2014, 552, 82-85.	0.8	2
123	(Invited) Point Defect Characterization of Group-III Nitrides by Using Monoenergetic Positron Beams. ECS Transactions, 2014, 61, 19-30.	0.3	14
124	Impact of the difference in power frequency on diamond-like carbon thin film coating over 3-dimensional objects. Thin Solid Films, 2014, 564, 45-50.	0.8	6
125	Defects in nitride-based semiconductors probed by positron annihilation. Journal of Physics: Conference Series, 2014, 505, 012009.	0.3	1
126	First-principles calculation of positron states and annihilation parameters for group-III nitrides. Journal of Physics: Conference Series, 2014, 505, 012010.	0.3	33



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127	Formation of low resistance ohmic contacts in GaN-based high electron mobility transistors with BCl <sub>3</sub> surface plasma treatment. Applied Physics Letters, 2013, 103, .	1.5	33
128	Impact of Se flux on the defect formation in polycrystalline Cu(In,Ga)Se <sub>2</sub> thin films grown by three stage evaporation process. Journal of Applied Physics, 2013, 113, 064907.	1.1	15
129	Excitonic emission dynamics in homoepitaxial AlN films studied using polarized and spatio-time-resolved cathodoluminescence measurements. Applied Physics Letters, 2013, 103, .	1.5	27
130	Vacancy-type defects in In <sub>x</sub> Ga <sub>1-x</sub> N grown on GaN templates probed using monoenergetic positron beams. Journal of Applied Physics, 2013, 114, .	1.1	15
131	Spatio-Time-Resolved Cathodoluminescence Studies on Freestanding GaN Substrates Grown by Hydride Vapor Phase Epitaxy. ECS Transactions, 2013, 50, 1-8.	0.3	2
132	Influence of wafer thinning process on backside damage in 3D integration. , 2013, , .		3
133	Vacancy-type defects introduced by plastic deformation of GaN studied using monoenergetic positron beams. Journal of Applied Physics, 2013, 114, .	1.1	8
134	Development of a sample chamber with humidity control for an atmospheric positron probe microanalyzer. Journal of Physics: Conference Series, 2013, 443, 012090.	0.3	1
135	Vacancy reactions near the interface between electroplated Cu and barrier metal layers studied by monoenergetic positron beams. Journal of Applied Physics, 2013, 114, 074510.	1.1	5
136	Material design of plasma-enhanced chemical vapour deposition SiCH films for low- <i>k</i> cap layers in the further scaling of ultra-large-scale integrated devices-Cu interconnects. Science and Technology of Advanced Materials, 2013, 14, 055005.	2.8	5
137	Characterization of Porous Structures in Advanced Low- <i>k</i> Films with Thin TaN Layers Using Monoenergetic Positron Beams. Japanese Journal of Applied Physics, 2013, 52, 106501.	0.8	9
138	Point defects introduced by InN alloying into In <sub>x</sub> Ga <sub>1-x</sub> N probed using a monoenergetic positron beam. Journal of Applied Physics, 2013, 113, 123502.	1.1	7
139	Time-resolved luminescence studies on AlN and high AlN mole fraction AlGa <sub>N</sub> alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 501-506.	0.8	6
140	Impacts of Si-doping and resultant cation vacancy formation on the luminescence dynamics for the near-band-edge emission of Al <sub>0.6</sub> Ga <sub>0.4</sub> N films grown on AlN templates by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2013, 113, .	1.1	98
141	Positron Annihilation Spectroscopy on Nitride-Based Semiconductors. Japanese Journal of Applied Physics, 2013, 52, 08JJ02.	0.8	26
142	The Effects of Plasma Treatments and Subsequent Atomic Layer Deposition on the Pore Structure of a <i>k</i> = 2.0 Low- <i>k</i> Material. ECS Journal of Solid State Science and Technology, 2013, 2, N103-N109.	0.9	7
143	Positron annihilation lifetime spectroscopy of mechanically milled protein fibre powders and their free volume aspects. Journal of Physics: Conference Series, 2013, 443, 012054.	0.3	0
144	Material characterization for advanced Si LSI process technology by means of positron annihilation. Journal of Physics: Conference Series, 2013, 443, 012067.	0.3	1

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145	Chemical effect of Si <sup>+</sup> ions on the implantation-induced defects in ZnO studied by a slow positron beam. <i>Journal of Applied Physics</i> , 2013, 113, 043506.	1.1	4
146	Positron annihilation studies on the behaviour of vacancies in LaAlO <sub>3</sub> /SrTiO <sub>3</sub> heterostructures. <i>Journal Physics D: Applied Physics</i> , 2012, 45, 445305.	1.3	9
147	Vacancy-Type Defects Introduced by Gas Cluster Ion-Implantation on Si Studied by Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 111801.	0.8	2
148	Variation of Chemical Vapor Deposited SiO <sub>2</sub> Density Due to Generation and Shrinkage of Open Space During Thermal Annealing. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 021101.	0.8	9
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